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STTH120R04TV

Ultrafast recovery diode

Main product characteristics

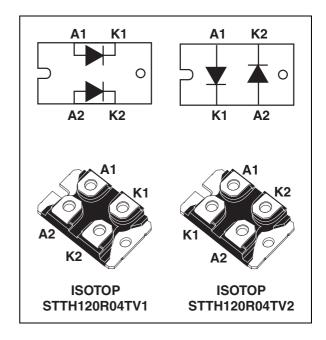
I _{F(AV)}	2 x 60 A
V _{RRM}	400 V
Tj	150° C
V _{F (typ)}	0.95 V
t _{rr (typ)}	31 ns

Features and benefits

- Ultrafast
- Very low switching losses
- High frequency and high pulsed current operation
- Low leakage current
- Insulated package:
 - ISOTOP
 Electrical insulation = 2500 V_{RMS}
 Capacitance = 45 pF

Description

The STTH120R04TV series uses ST's new 400 V planar Pt doping technology. The STTH120R04 is specially suited for switching mode base drive and transistor circuits, such as welding equipment.



Order codes

Part Number	Marking
STTH120R04TV1	STTH120R04TV1
STTH120R04TV2	STTH120R04TV2

Characteristics STTH120R04TV

1 Characteristics

Table 1. Absolute ratings (limiting values per diode at 25° C, unless otherwise specified)

Symbol	Parameter				Unit
V _{RRM}	Repetitive peak reverse voltage	Repetitive peak reverse voltage			V
V_{RSM}	Non repetitive peak reverse voltage			400	V
I _{F(RMS)}	RMS forward current	RMS forward current Per diode			
1	Average forward current S = 0.5	Per diode	T _c = 75° C	60	Α
I _{F(AV)}	Average forward current, $\delta = 0.5$	Per package	T _c = 70° C	120	Α
I _{FRM}	Repetitive peak forward current $t_p = 5 \mu s$, $F = 1 kHz square$		1800	Α	
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			700	Α
T _{stg}	Storage temperature range			-65 to + 150	°C
Tj	Maximum operating junction temperature			150	°C

Table 2. Thermal parameters

Symbol	Parameter		Value	Unit
D	lunchion to once		0.8	
$R_{th(j-c)}$	Junction to case Total	0.45	° C/W	
R _{th(c)}	Coupling thermal resistance		0.1	

When the diodes are used simultaneously: $\Delta T_{j(diode1)} = P_{(diode1)} \ x \ R_{th(j\text{-}c)} \ (\text{per diode}) + P_{(diode2)} \ x \ R_{th(c)}$

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Povorco logizado gurrant	T _j = 25° C	V - V			60	^
I _R ⁽¹⁾ Reverse leakage current	T _j = 125° C	$V_R = V_{RRM}$		60	600	μΑ	
		T _j = 25° C				1.5	
V _F ⁽²⁾ Forward voltage drop	Forward voltage drop	T _j = 100° C	I _F = 60 A		1.05	1.3	V
		T _j = 150° C			0.95	1.2	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2$ %

To evaluate the conduction losses use the following equation:

$$P = 0.9 \times I_{F(AV)} + 0.005 \times I_{F}^{2}(RMS)$$

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^{2.} Pulse test: $t_{\rm p}$ = 380 μ s, δ < 2 %

STTH120R04TV Characteristics

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
		$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$			80	
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		40	55	ns
		$I_F = 1 \text{ A, } dI_F/dt = -200 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		31	45	
I _{RM}	Reverse recovery current	$I_F = 60 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 320 \text{ V}, T_j = 125^{\circ} \text{ C}$		11	16	Α
S	Softness factor	$I_F = 60 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 320 \text{ V}, T_j = 125^{\circ} \text{ C}$		0.4		
t _{fr}	Forward recovery time	$I_F = 60 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.5 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$		600		ns
V _{FP}	Forward recovery voltage	$I_F = 60 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s},$ $T_j = 25^{\circ} \text{ C}$		3.2		V

Figure 1. Conduction losses versus average current

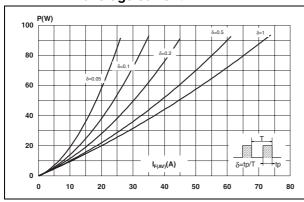


Figure 2. Forward voltage drop versus forward current

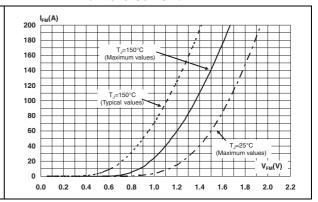
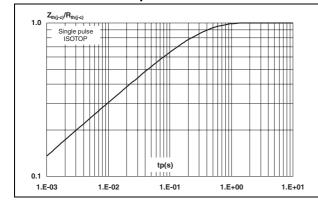
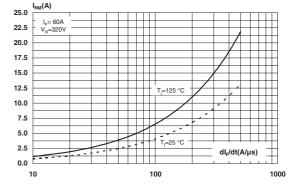


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)

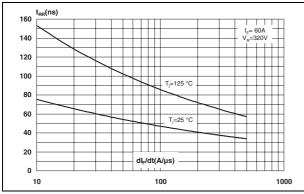




Characteristics STTH120R04TV

Figure 5. Reverse recovery time versus dl_F/dt (typical values)

Figure 6. Reverse recovery charges versus dl_F/dt (typical values)



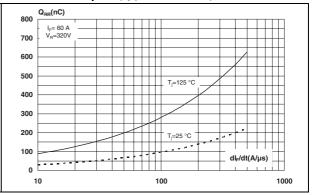
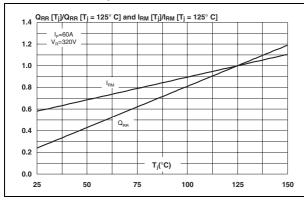


Figure 7. Relative variations of dynamic parameters versus junction temperature

Figure 8. Transient peak forward voltage versus dl_F/dt (typical values)



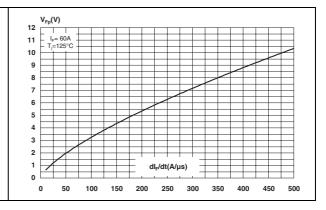
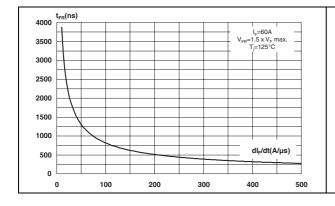
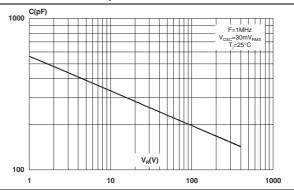


Figure 9. Forward recovery time versus dl_F/dt Figure 10. Junction cal (typical values)

Junction capacitance versus reverse voltage applied (typical values)





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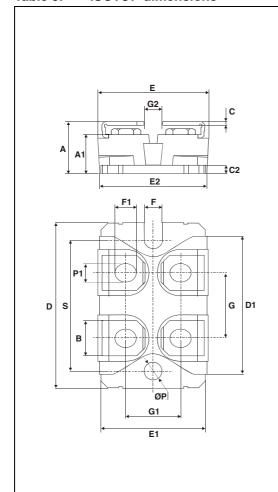
STTH120R04TV Package information

2 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Table 5. ISOTOP dimensions



		Dimer	nsions		
Ref.	Millim	neters	Inc	hes	
	Min.	Max.	Min.	Max.	
Α	11.80	12.20	0.465	0.480	
A1	8.90	9.10	0.350	0.358	
В	7.8	8.20	0.307	0.323	
С	0.75	0.85	0.030	0.033	
C2	1.95	2.05	0.077	0.081	
D	37.80	38.20	1.488	1.504	
D1	31.50	31.70	1.240	1.248	
Е	25.15	25.50	0.990	1.004	
E1	23.85	24.15	0.939	0.951	
E2	24.80 typ.		0.976 typ.		
G	14.90	15.10	0.587	0.594	
G1	12.60	12.80	0.496	0.504	
G2	3.50	4.30	0.138	0.169	
F	4.10	4.30	0.161	0.169	
F1	4.60	5.00	0.181	0.197	
Р	4.00	4.30	0.157	0.69	
P1	4.00	4.40	0.157	0.173	
S	30.10	30.30	1.185	1.193	

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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Ordering information STTH120R04TV

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH120R04TV1	STTH120R04TV1	ISOTOP	27 g	10	Tube
STTH120R04TV2	STTH120R04TV2	ISOTOP	27 g	10	Tube

4 Revision history

Date	Revision	Description of Changes
31-Mar-2007	1	First issue

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